Contents of Vol. 192

Issue 1

Electronics and Optics

Breakdown of SiO_2 thin films grown in dry O_2 1
M. Badila, C. Pavelescu and O. Popa (Bucharest, Romania)

Hydrogenized silicon nitride conductivity of optically pumped localized states 7
S. N. Kuznetsov and V. A. Gurtov (Petrozavodsk, U.S.S.R.)

Electrical and optical properties of vacuum-evaporated indium–tin oxide films with high electron mobility 17
T. Nagatomo, Y. Maruta and O. Omoto (Tokyo, Japan)

Structural influences on the laser damage resistance of optical oxide coatings for use at 1064 nm . 27
E. Hacker, H. Lauth, J. Meyer and P. Weissbrodt (Jena, G.D.R.), R. Wolf and G. Zscherpe (Mittweida, G.D.R.) and H. Heyer (Jena, G.D.R.)

Slow ramp voltage technique for investigation of breakdown voltage distribution in thin plasma-nitrided SiO_2 films 41
G. Slavcheva (Sofia, Bulgaria)

Shallow n^+ junction formation using ion mixing of tungsten at elevated temperatures 59
H. Jiang and C. S. Petersson (Kista, Sweden) and G. Holmén (Gothenberg, Sweden)

Metallurgical and Protective Layers

Degradation mechanisms of the contact between metallic films and alkali halide crystals 73
S. A. Varchenya, A. Simanovskis and S. V. Stolyarova (Salaspils, U.S.S.R.)

Pinhole plugging characteristics of silica/iron/silver protective coatings in atomic oxygen environments 79
J. H. Sanders and B. J. Tatarchuk (Auburn, AL, U.S.A.)

Influence of heat treatments on the cohesion and adhesion strength of plasma-sprayed deposits . 97
J. Hennaut, J. Othmezouri and J. Charlier (Brussels, Belgium)

Preparation and Characterization

Growth by molecular beam epitaxy of indium antimonide on cleaved and on polished barium fluoride 111
J. L. Davis (Washington, D.C., U.S.A.)

Annealing and crystallization processes in a hydrogenated amorphous Si–C alloy film 121
D. K. Basa (Bhubaneswar, India) and F. W. Smith (New York, NY, U.S.A.)

In situ electron beam irradiation induced in-plane orientation of europium thin film grown by the molecular beam epitaxy technique 135
A. Maeda, T. Satake, T. Fujimori, S. Maeda and H. Kuroda (Ibaraki, Japan)

Structure of PbTe films grown on polyimide 141
N. N. Zheleva (Sofia, Bulgaria), J. Stoemenos (Thessaloniki, Greece), M. H. Koparanova and D. B. Kushev (Sofia, Bulgaria)

Rutherford backscattering spectroscopy and X-ray photoelectron spectroscopy studies of thin glass films prepared by laser evaporation 149
E. E. Khawaja, F. F. Al-Adel, A. B. Hallak, M. M. Al-Kofahi and M. A. Salim (Dhahran, Saudi Arabia)

Hydrogen bonding and its temperature dependence in vinyl chloride–vinyl acetate–vinyl alcohol terpolymer: a study using the IR absorption technique 157
V. S. Panwar, R. Singh and P. C. Mehendru (New Delhi, India) and N. P. Gupta (Saharanpur, India)

Nucleation and growth of thin gold films on NaCl(100) cleavage planes under carefully controlled conditions 163
R. Conrad and M. Harsdorff (Hamburg, F.R.G.)

Langmuir–Blodgett and Related Films

Use of X-ray photoelectron spectroscopy in the measurement of protein orientation on surfaces . 173
R. P. Vasquez and R. Margalit (Pasadena, CA, U.S.A.)

Condensed Matter Film Behaviour

Electromigration threshold of thin-film conductors 181
V. M. Koleshko and I. V. Kiryushin (Minsk, U.S.S.R.)

Letters

The transition from substrate-dependent to bulk structures in Langmuir–Blodgett multilayers of 22-tricosenoic acid L1
I. Robinson and J. R. Sambles (Exeter, U.K.)

Optical properties of electrodeposited $CuInSe_2$ thin films. L5
P. Garg and J. C. Garg (Jaipur, India) and A. C. Rastogi (New Delhi, India)

Etch rate behaviour of SiO_2 films chemically vapour deposited at low temperatures in TEOS–O_2–N_2 system L9
I. Kleps and C. Pavelescu (Bucharest, Romania)

Issue 2

Electronics and Optics

Some formation factors affecting the dissolution behaviour of anodic oxide films on aluminium in H_3PO_4 193
A. A. Mazhar, F. El-Taib Heakal and Kh. M. Awad (Giza, Egypt)

Optical properties of amorphous carbon films formed by r.f. plasma deposition from methane . . . 201
F. M. El-Hossary and D. J. Fabian (Glasgow, U.K.) and A. P. Webb (Towcester, U.K.)

Optical absorption of amorphous WO_3 and binding state of tungsten 211
A. Temmink, O. Anderson and K. Bange (Mainz, F.R.G.), H. Hantsche and X. Yu (Berlin, F.R.G.)

Application of a computer model for determining the contribution of the fundamental conduction mechanisms in discontinuous metal films—aluminium on NaCl 219
M. Błażej and E. Dobierzewska-Mozrzymas (Wrocław, Poland)

Near IR optical properties of sputtered InN films 227
K. L. Westra and M. J. Brett (Edmonton, Alb., Canada)

Metallurgical and Protective Layers

Low temperature boron coatings by microwave plasma assisted chemical vapour deposition . . . 235
V. Cholet, R. Herbin and L. Vandenbulcke (Orleans, France)

Tribological behaviour and mechanical properties of physical-vapour-deposited hard coatings: TiN_x, ZrN_x, TiC_x, TiC_x/i-C 253
J. Vetter and R. Rochotzki (Karl-Marx-Stadt, G.D.R.)

Influence of angular distribution of particle incidence on properties of sputtered TiN films 263
A. Neidhardt, U. Reinhold, E. Schroeter and W. Wuttke (Zwickau, G.D.R.)

Internal stress and structure of ultrahigh vacuum evaporated chromium and iron films and their dependence on substrate temperature and oxygen partial pressure during deposition 277
G. Thurner and R. Abermann (Innsbruck, Austria)

Preparation and Characterization

Unique properties of molecular beam epitaxy silicon on sapphire using *in situ* high-temperature substrate annealing compared with chemically vapor deposited silicon on sapphire. 287
E. D. Richmond (Washington, DC, U.S.A.), J. G. Pellegrino (Gaithersburg, MD, U.S.A.), M. E. Twigg (Fort Washington, MD, U.S.A.), S. Qadri (Washington, DC, U.S.A.) and M. T. Duffy (Princeton, NJ, U.S.A.)

Properties of hydrogenated amorphous Si–N films prepared by r.f. magnetron sputtering with emphasis on the non-stoichiometric region 295
R. Banerjee, A. K. Bandyopadhyay, J. K. Rath, A. K. Batabyal and A. K. Barua (Calcutta, India)

The chemistry of the growth of ZnS deposited by r.f. sputtering onto cadmium stannate. I: the interface 309
J. M. Blackmore, G. W. Blackmore, D. C. Rodway and M. J. Slater (Great Malvern, U.K.)

The chemistry of the growth of ZnS deposited by r.f. sputtering onto cadmium stannate. II: the bulk 321
J. M. Blackmore, G. W. Blackmore, O. D. Dosser and M. J. Slater (Great Malvern, U.K.)

Columnar structure of obliquely deposited cobalt films prepared at low substrate temperatures . . 335
T. Hashimoto (Tottori, Japan), K. Okamoto (Chiba, Japan), H. Fujiwara (Hiroshima, Japan), K. Itoh, K. Hara and M. Kamiya (Kumamoto, Japan)

Kinetic processes in epitaxy of $Ga_xIn_{1-x}As$ on InP(100) by hydride vapour phase epitaxy 343
M. Cadoret, L. Chaput, H. Banvillet, A. Porte, C. Pariset and R. Cadoret (Aubiere, France)

Kinetic measurements of oxygen dissolution into niobium substrates: *in situ* X-ray photoelectron spectroscopy studies 351
B. R. King and H. C. Patel (Auburn, AL, U.S.A.), D. A. Gulino (Athens, OH, U.S.A.) and B. J. Tatarchuk (Auburn, AL, U.S.A.)

Measurements of reactive O_2 sticking coefficients and oxidation rates at niobium oxide surfaces . 371
B. R. King and B. J. Tatarchuk (Auburn, AL, U.S.A.)

Langmuir–Blodgett and Related Films

Substituted silicon phthalocyanine Langmuir–Blodgett film and its possible use in electronic devices 383
Y. L. Hua, D. P. Jiang and Z. Y. Shu (Sinica, P.R.C.), M. C. Petty, G. G. Roberts and M. M. Ahmad (Durham, U.K.)

The deposition and characterization of phosphatidic acid Langmuir–Blodgett films 391
D. F. Cui, V. A. Howarth, M. C. Petty, H. Ancelin and J. Yarwood (Durham, U.K.)

Author Index 397